

In the Specification:

On page 1, after the title insert the following:

**RELATED APPLICATIONS**

This is a U.S. national stage of application No. PCT/DE2003/004197, filed on 18 December 2003.

This patent application claims the priority of German patent application nos. 102 61 426.1 and 103 06 779.5, filed 30 December 2002 and 18 February 2003, respectively, the disclosure content of which is hereby incorporated by reference.

**FIELD OF THE INVENTION**

On page 1, before line 10, insert the following heading:

**BACKGROUND OF THE INVENTION**

On page 3, before line 11, insert the following heading:

**SUMMARY OF THE INVENTION**

On page 3, amend the paragraph beginning on line 11 as follows:

It is an object of the present invention to ~~specify~~ provide a method for roughening a surface of a body which is suitable for many different materials.

On page 3, delete the paragraph beginning on line 15 through line 18 in its entirety.

On page 3, amend the paragraph beginning on line 20 as follows:

The invention makes use of the fundamental idea according to which the problem of the selectivity of the etching methods used can be alleviated by additionally using a further auxiliary mask besides the masking by the small polystyrene balls. Said auxiliary mask is composed of a material which is both different from the material of the body to be etched and different from the material of the balls. With the aid of this additional mask, the etching process can be subdivided into two steps, in a first step the ~~structure~~ arrangement of the balls arranged on the surface being transferred into the auxiliary mask. In a second step, the ~~structure~~ arrangement of the auxiliary mask is then transferred into the surface of the body to be etched.

On page 4, amend the paragraph beginning on line 16 as follows:

A One aspect of the invention is directed to a method for roughening a surface of a body  
~~is specified,~~ which comprises the following steps:

On page 6, amend the paragraph beginning on line 11 as follows:

By way of example, consideration is also given to using an ~~inductively~~ inductive coupled plasma etching method (ICP) as dry etching method.

On page 8, amend the paragraph beginning on line 14 as follows:

A fluorine process may advantageously be employed in this case, a gas mixture of  $\text{CHF}_3$  and argon being used. A standard RIE (reactive ion etching) installation with a parallel plate reactor is usually used in this case.

On page 8, amend the paragraph beginning on line 19 as follows:

The second etching step may be carried out for example by means of an ICP (inductively coupled plasma) installation, a mixture of CH<sub>4</sub> and H<sub>2</sub> being used as etching gas.

On page 8, amend the paragraph beginning on line 23 as follows:

~~Furthermore,~~ Another aspect of the invention is directed to an optoelectronic component having a semiconductor body ~~is also specified~~. Said semiconductor body contains aluminum gallium indium phosphite or aluminum gallium indium nitride. Furthermore, the surface of the body is patterned with structures, the following holding true for the width of the structures in comparison with the depth of the structures or the etching depth: ~~0.25~~ 0.1 < t/b < 10 ~~5~~. ~~Furthermore, the same component is specified but the semiconductor body contains aluminum gallium indium nitride instead of aluminum gallium indium phosphite.~~ Such optoelectronic components, for example LEDs, can be produced for the first time with the aid of the method presented here. The methods disclosed in the prior art are not suitable for producing the ratio of t to b described here.

On page 9, before line 11, insert the following heading:

## **BRIEF DESCRIPTION OF THE DRAWINGS**

On page 9, before line 27, insert the following heading:

## **DETAILED DESCRIPTION OF THE DRAWINGS**

On page 11, amend the paragraph beginning on line 7, as follows:

The structures 4 may ~~either~~ be positioned regularly along a grid defined in the front end by the arrangement of the mask bodies 3. This is disclosed by H.W. Deckman et al., "National Lithography", Appl. Phys. Lett. 41(4), 16 August 1982, pp. 377-379. However, the structures 4 may also be distributed randomly over the surface of the body 1.

On page 11, add the following as the last paragraph:

The scope of protection of the invention is not limited to the examples given hereinabove. The invention is embodied in each novel characteristic and each combination of characteristics, which includes every combination of any features which are stated in the claims, even if this combination of features is not explicitly stated in the claims.